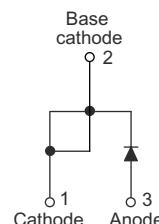


Schottky Rectifier, 10 A



FEATURES

- 150°C T_J operation
- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS
- Designed and qualified according to JEDEC-JESD47



TO-220AC

DESCRIPTION

The MBR1045 Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150°C junction temperature.

APPLICATIONS

- Switching mode power supplies
- Converters
- Freewheeling diodes
- Reverse battery protection.

PRODUCT SUMMARY

Package	TO-220AC
$I_{F(AV)}$	10A
V_R	45V
V_F at I_F	0.57V
I_{RM} max.	15mA at 125°C
T_J max.	150°C
Diode variation	Single die
E_{AS}	8 mJ

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUE	UNIT
$I_{F(AV)}$	Rectangular waveform	10	A
I_{FRM}	$T_J = 135^\circ\text{C}$	20	A
V_{RRM}		45	V
I_{FSM}	$t_p = 5 \mu\text{s}$ sine	1060	A
V_F	10 A _{pk} , $T_J = 125^\circ\text{C}$	0.57	V
T_J	Range	-65 to 150	°C

VOLTAGE RATINGS

PARAMETER	SYMBOL	MBR1045	UNIT
Maximum DC reverse voltage	V_R	45	V
Maximum working peak reverse voltage	V_{RWM}		

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUE	UNIT
Maximum average forward current	$I_{F(AV)}$	$T_C = 131^\circ C$, rated V_R		10	A
Peak repetitive forward current	I_{FRM}	Rated V_R , square wave, 20 kHz, $T_C = 135^\circ C$		20	A
Non-repetitive peak surge current	I_{FSM}	5 μs sine or 3 μs rect.pulse	Following any rated load condition and with rated V_{RRM} applied	1060	A
		Surge applied at rated load condition half wave single phase 60 Hz		150	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25^\circ C$, $I_{AS} = 2A$, $L = 4mH$		8	mJ
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum $V_A = 1.5 \times V_R$ typical		2	A

ELECTRICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUE	UNIT	
Maximum forward voltage drop	$V_{FM}^{(1)}$	20A	$T_J = 25^\circ C$	0.84	V	
		10A	$T_J = 125^\circ C$	0.57		
		20A		0.72		
Maximum instantaneous reverse current	$I_{RM}^{(1)}$	$T_J = 25^\circ C$	Rated DC voltage	0.1	mA	
		$T_J = 125^\circ C$		15		
Maximum junction capacitance	C_T	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHZ) $25^\circ C$		600	pF	
Typical series inductance	L_s	Measured from top of terminal to mounting plane		8	nH	
Maximum voltage rate of change	dV/dt	Rated V_R		10000	V/ μ s	
Threshold voltage	$V_{F(TO)}$	$T_J = T_J$ maximum		0.345	V	
Forward slope resistance	r_t			17.6	m Ω	

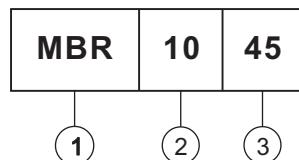
Note

(1) Pulse width < 300 μs , duty cycle < 2%

THERMAL - MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUE	UNIT	
Maximum junction temperature range	T_J			-65 to 150	°C	
Maximum storage temperature range	T_{stg}			-65 to 175		
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		2	°C/W	
Typical thermal resistance, case to heatsink	R_{thCS}			0.5		
Approximate weight				2	g	
				0.07	oz.	
Mounting torque	minimum maximum			6 (5)	kgf · cm (lbf · in)	
				12 (10)		
Marking device		Case style TO-220AC		MBR1045		

Ordering Information Table

Device code


- 1**
- 2**
- 3**

- Schottky MBR series
- Current rating (10 = 10A)
- Voltage ratings

45=45V

Fig.1 Maximum forward voltage drop characteristics

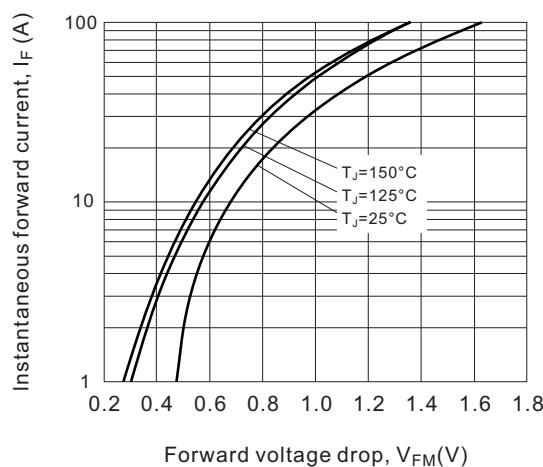


Fig.2 Typical values of reverse current vs. reverse voltage

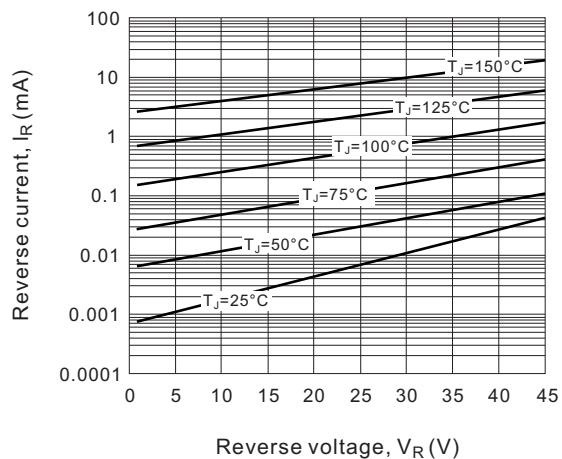


Fig.3 Typical junction capacitance vs. reverse voltage

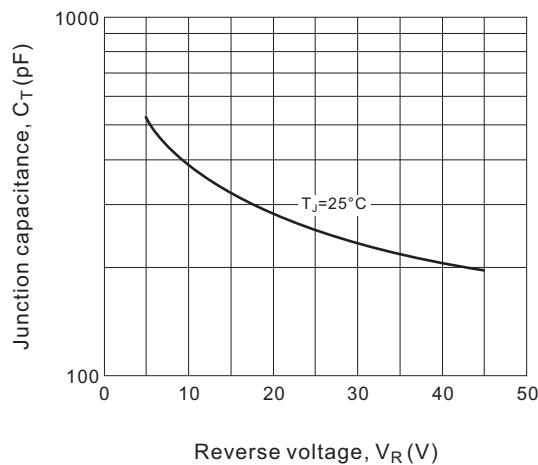


Fig.4 Maximum allowable case temperature vs. average forward current

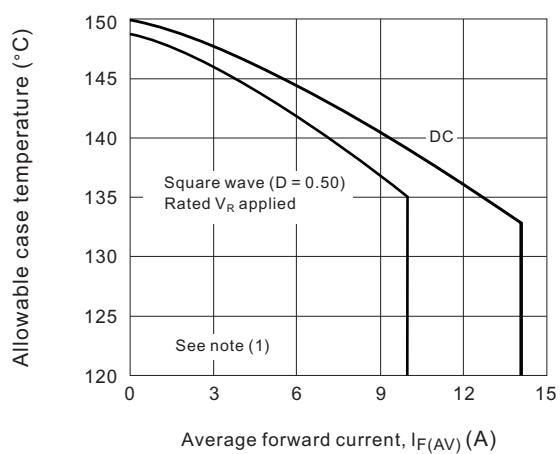
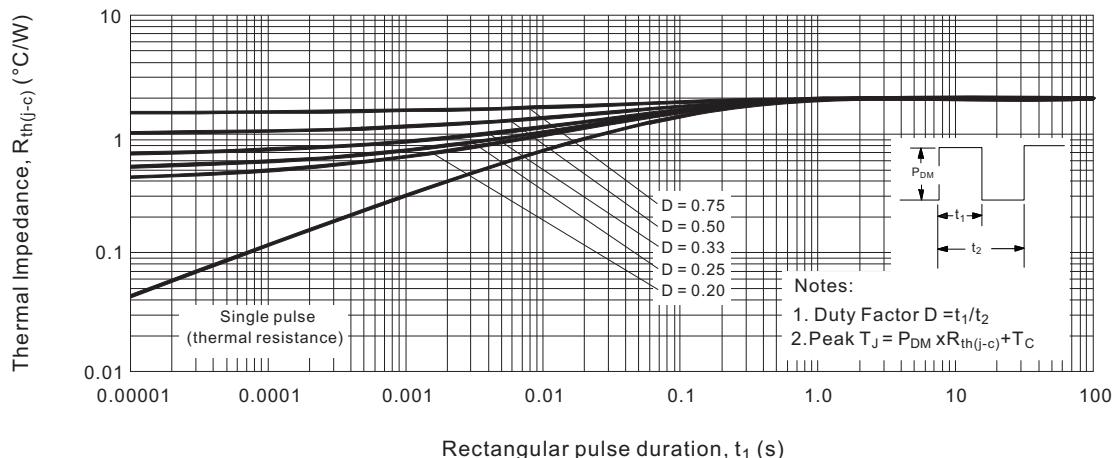
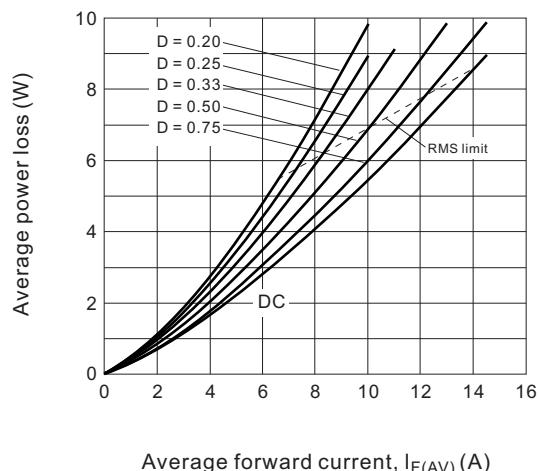
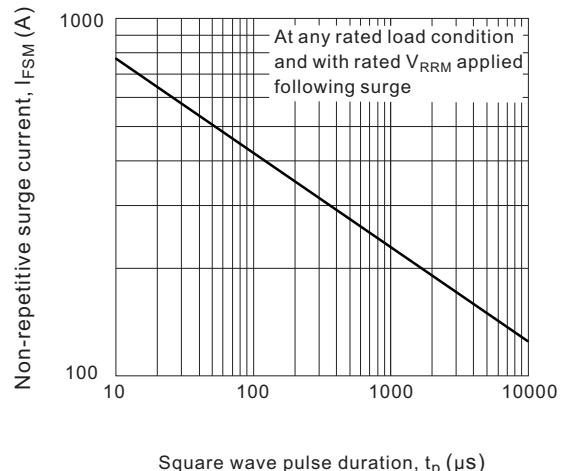


Fig.5 Maximum thermal impedance $R_{th(j-c)}$ characteristics

Fig.6 Forward power loss characteristics

Fig.7 Maximum non-repetitive surge current

Note

(1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
 $P_d = \text{Forward power loss} = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig.6);
 $P_{dREV} = \text{Inverse power loss} = V_{R1} \times I_R (1-D)$; I_R at $V_{R1} = \text{Rated } V_R$

